

November 18, 2003

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/650,600 08/28/03

Tai Min et al.

MAGNETIC RANDOM ACCESS MEMORY DESIGNS
WITH CONTROLLED MAGNETIC SWITCHING
MECHANISM BY MAGNETOSTATIC COUPLING

Grp. Art Unit: _____

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

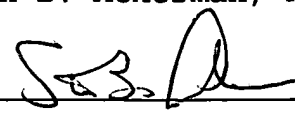
The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on November 21, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 11/21/03

U.S. Patent 6,242,770 to Bronner et al., "Diode Connected to a Magnetic Tunnel Junction and Self Aligned with a Metallic Conductor and Method for Forming the Same," teaches a method for forming thin film conductors as word and bit lines so that the MTJ device is in close proximity to a lower line and a diode is located below that line.

U.S. Patent 6,166,948 to Parkin et al., "Magnetic Memory Array with Magnetic Tunnel Junction Memory Cells Having Flux-Closed Free Layers," discloses that sub-micron dimensions are needed to be competitive with DRAM memories in the range of 10-100 Mbit capacities.

U.S. Patent 5,757,695 to Shi et al., "MRAM with Aligned Magnetic Vectors," teaches the formation of an ellipsoidal MTJ cell wherein the magnetization vectors are aligned along the length (major axis) of the cell and which do not present variously oriented edge domains, high fields and poles at the ends of the element.

U.S. Patent 6,376,260 to Chen et al., "Magnetic Element with Improved Field Response and Fabricating Method Thereof," teaches an improved fabrication method in which the magnetic element includes a first electrode (a fixed layer), a second electrode (a free layer) and a spacer layer between them.

HT-02-015

U.S. Patent 6,005,800 to Koch et al., "Magnetic Memory Array with Paired Asymmetric Memory Cells for Improved Write Margin," discusses the problem that results when writing to one specific cell also affects the magnetization directions of adjacent cells that are not being addressed.

U.S. Patent Application HT-02-014, Serial No. 10/647,716, filed 08/25/03, assigned to the same assignee as the current invention, discusses the use of magnetic tunnel junctions (MTJ) as storage elements (cells) in non-volatile memory cell arrays, called magnetic random access memories (MRAM).

Sincerely,

A handwritten signature in black ink, appearing to be 'SBA', written over a horizontal line.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Document Number (Optional)

HT-02-015

Application Number

10/650,600

Applicant

Tai Min et al.

Filing Date

08/28/03

Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6242720	6/5/01	Bronner et al.	257	295	8/31/98
	6166948	12/26/00	Parkin et al.	365	173	9/3/99
	5757695	5/26/98	Shi et al.	365	158	2/5/97
	6376260	4/23/02	Chen et al.	438	3	4/5/01
	6005800	12/21/99	Koch et al.	365	173	11/23/98



FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

U.S. Patent Application HT-02-014, Serial No.
10/647,716, filed 08/25/03, assigned to the
same assignee.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.